

ABSTRACT OF THE DISCLOSURE

A semiconductor device with high reliability is provided in which an insulating property of an insulating layer is high and connection failure is prevented.

5 The semiconductor device includes: a silicon substrate; a low-temperature aluminum film formed on silicon substrate and including a polycrystal; and a high-temperature aluminum film. An opening is formed in a surface of a high-temperature aluminum film by a crystal grain
10 boundary. A distance between side walls of the opening becomes small as closer to silicon substrate.